

Critical fields, thermally activated transport, and critical current density of β -FeSe single crystals

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We present critical fields, thermally activated flux flow (TAFF), and critical current density of tetragonal phase β -FeSe single crystals. The upper critical fields $H_{c2}(T)$ for $H \parallel (101)$ and $H \perp (101)$ are nearly isotropic and are likely governed by the Pauli limiting process. The large Ginzburg-Landau parameter $\kappa \sim 72.3(2)$ indicates that β -FeSe is a type-II superconductor with a smaller penetration depth than in Fe(Te, Se). The resistivity below T_c follows Arrhenius TAFF behavior. For both field directions below 30 kOe, single-vortex pinning is dominant, whereas collective creep becomes important above 30 kOe. The critical current density J_c from M - H loops for $H \parallel (101)$ is about five times larger than for $H \perp (101)$, yet much smaller than in other iron-based superconductors.

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I. INTRODUCTION

Among iron-based superconductors, the tetragonal β -FeSe has triggered great interest because of its simple structure and superconductivity below about 8 K without any carrier doping.¹ Besides β -FeSe, superconductivity has also been discovered in binary Fe(Te, Se) and Fe(Te, S) materials.^{2,3} These materials also have a Fermi surface similar to that of FePn (Pn = P, As)-based superconductors,⁴ even though they have FeCh (Ch = Te, Se, S) layers, as opposed to FePn layers, stacked along the c axis. Understanding this similarity is rather important. The binary FeCh material β -FeSe has another notable characteristic: Application of pressure leads to a significant enhancement of T_c up to 37 K at around 9 GPa, the third-highest known critical temperature for any binary compound.⁵

In order to study anisotropic and intrinsic physical properties of materials, single crystals are required. When compared to Fe(Te, Se) and Fe(Te, S), the extremely complex phase diagram of FeSe makes impurities such as α -FeSe and Fe₇Se₈ ubiquitous in as-grown crystals. Sometimes polycrystals also impede the understanding of β -FeSe.⁶⁻¹⁰

Here, we report intrinsic superconducting properties of β -FeSe single crystals. These include critical fields H_{c2} and H_{c1} , thermally activated flux flow (TAFF) behavior, and the critical current density J_c . Our results show that β -FeSe is a type-II superconductor with large Ginzburg-Landau parameter κ and smaller critical current density when compared to other iron-based superconductors. Single-vortex pinning dominates vortex dynamics below 30 kOe, whereas collective creep becomes important at higher magnetic fields.

II. EXPERIMENT

Details of synthesis and structural characterization are explained elsewhere.¹¹ Thin Pt wires were attached to electrical contacts made of Epotek H20E silver epoxy for a standard four-probe measurement, with current flowing in the crystal plane. Sample geometries were measured with a Nikon SMZ-800 optical microscope with 10- μ m resolution. Magnetization and resistivity measurements were carried out in Quantum Design MPMS and PPMS, respectively.

III. RESULTS AND DISCUSSION

Figure 1(a) shows the temperature dependence of the in-plane resistivity $\rho(T)$ below 300 K. The residual resistivity ratio (RRR) of 14 is double that of the hexagonal crystals,⁶ indicating good sample quality. The curvature of $\rho(T)$ changes at about 100 K [Fig. 1(a), inset (a)] due to structural and magnetic transitions, in agreement with previous results.^{1,6,12} With a further decrease in temperature, superconductivity emerges with $T_{c,\text{onset}} \simeq 11.4$ K and $T_{c,0} \simeq 8.1$ K [Figs. 1(a) and 1(b)], similar to reported values in the literature.⁶ Figure 1(b) presents the ac susceptibility of FeSe single crystal for a field perpendicular to the crystal plane. The corresponding superconducting volume fraction at $T = 1.8$ K is about 70%, confirming the bulk nature of superconductivity. The XRD pattern of a single crystal [Fig. 1(b) inset] reveals that the crystal surface is normal to the (101) direction, which is also similar to previous results.^{6,8}

Figures 2(a) and 2(b) shows the temperature dependence of $\rho(T)$ in various fields for $H \parallel (101)$ and $H \perp (101)$. T_c shifts to a lower temperature without obvious broadening for both directions with the increase in magnetic fields. Temperature dependence of the upper critical fields $H_{c2}(T)$ was determined from resistivity drops to 90%, 50%, and 10% of the normal-state resistivity $\rho_n(T, H)$ [Fig. 2(c)]. The normal-state resistivity was determined by linearly extrapolating the normal-state behavior above the onset of superconductivity. The $H_{c2}(T)$ curves are nearly linear and the initial slopes $dH_{c2}/dT|_{T_c}$ are given in Table I. The slopes are nearly identical for both field directions, and the anisotropy of the upper critical field $\gamma(T) = H_{c2,H \perp (101)}(T)/H_{c2,H \parallel (101)}(T)$ is also isotropic within the experimental error.

Within the weak coupling BCS theory¹³ and using the slope determined from the midpoint of resistive transition with $T_c = 9.8$ K, we can estimate $H_{c2}(0) = -0.693T_c(dH_{c2}/dT|_{T_c}) = 180(4)$ kOe for both field directions. The results are close to the Pauli paramagnetic limit $H_P(0) = 1.84T_c = 180(4)$ kOe.¹⁴ This implies that the spin-paramagnetic effect may be the dominant pair-breaking mechanism in FeSe for both field directions, similar to Fe(Te, Se) and Fe(Te, S).^{15,16} The superconducting coherence length $\xi(0)$ estimated using the Ginzburg-Landau formula $H_{c2}(0) = \Phi_0/2\pi\xi^2(0)$, where $\Phi_0 = 2.07 \times 10^{-15}$ Wb is the flux quantum, is $\xi(0) = 4.28(5)$ nm, which is somewhat larger than Fe(Te, Se) and Fe(Te, S).^{15,16}

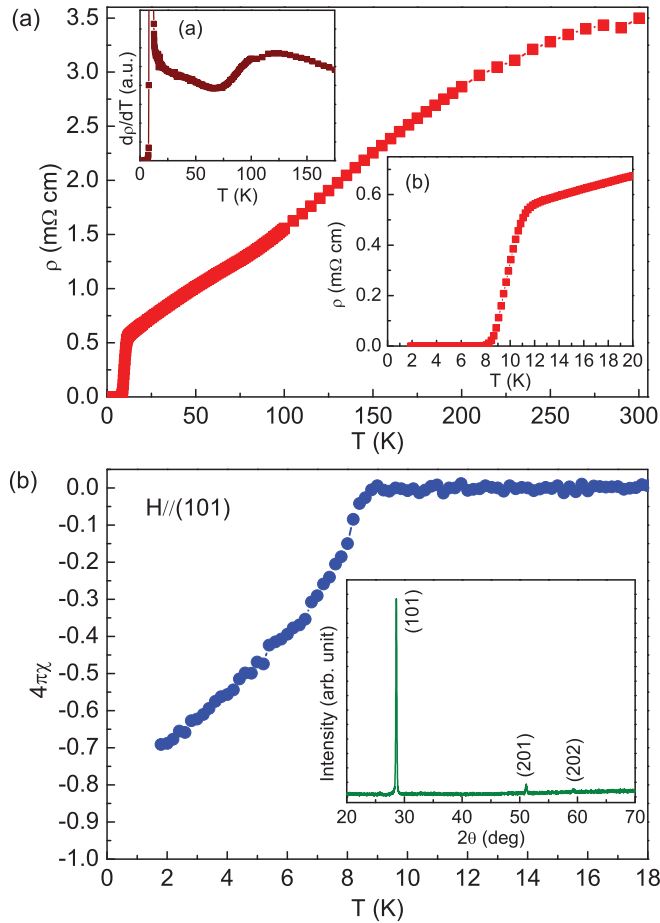


FIG. 1. (Color online) (a) Temperature dependence of the in-plane resistivity $\rho(T)$ of β -FeSe single crystals. Inset (a) shows a derivative of resistivity data $d\rho/dT$ as a function of temperature. Inset (b) shows an enlarged resistivity curve near T_c . (b) Temperature dependence of dc magnetic susceptibility of β -FeSe single crystals for $H = 10$ Oe along the (101) plane. Inset: single crystal x-ray diffraction (XRD) pattern of β -FeSe.

According to the TAFF theory, the $\ln\rho - 1/T$ in the TAFF region can be described using an Arrhenius relation^{17,18}

$$\ln\rho(T, H) = \ln\rho_0(H) - U_0(H)/T, \quad (1)$$

where $\ln\rho_0(H) = \ln\rho_{0f} + U_0(H)/T_c$ is the temperature-independent constant and $U_0(H)$ is the apparent activated energy. Hence, $\ln\rho(T, H)$ versus $1/T$ should be linear in the TAFF region. As shown in Figs. 3(a) and 3(b), the Arrhenius relation (solid lines) can fit the experimental data very well for both field directions. The results are shown in the common logarithmic scale in the figures, but we calculate

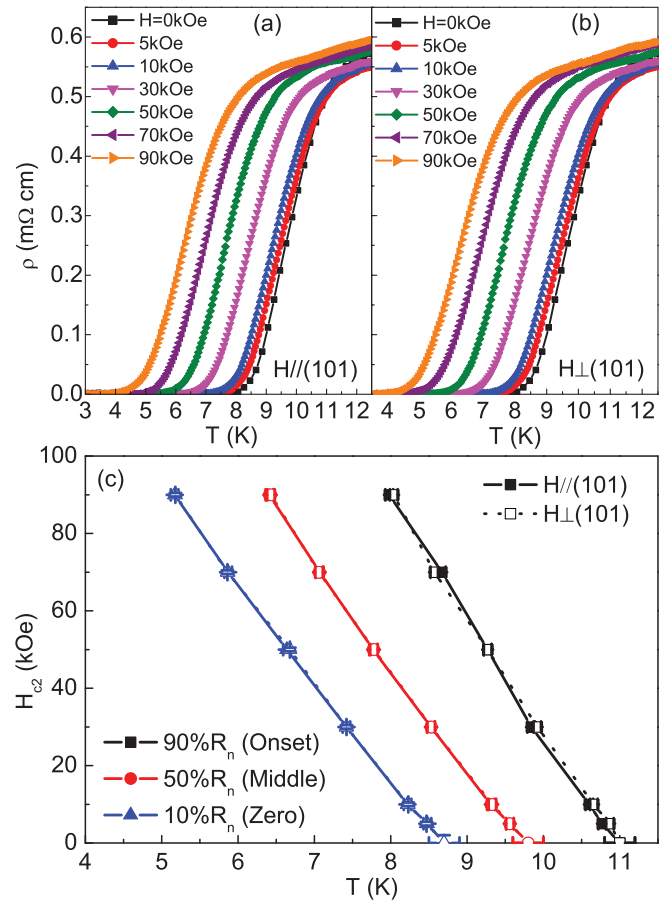


FIG. 2. (Color online) Temperature dependence of the resistivity $\rho(T)$ of β -FeSe single crystals for (a) $H||(101)$ and (b) $H\perp(101)$ in a magnetic field up to 90 kOe. (c) Temperature dependence of the resistive upper critical field $H_{c2}(T)$ corresponding to three defined temperatures for both field directions (see text).

them in the natural one. The obtained U_0 's are similar for both field directions. They are comparable to that in Fe(Te, S) and much smaller than that in Fe(Te, Se).^{19,20} This good linear behavior indicates that the temperature dependence of thermally activated energy (TAE) $U(T, H)$ is approximately linear, i.e., $U(T, H) = U_0(H)(1 - T/T_c)$.^{17,18} The $\log\rho(T, H)$ lines for different fields extrapolate to the same temperature T_{cross} , which should equal T_c .¹⁹ The extrapolated temperatures are about 11.1 K for both $H||(101)$ and $H\perp(101)$. Moreover, $\ln\rho_0(H) - U_0(H)$ shows linear behavior for both field directions [Fig. 3(c)]. Fits using $\ln\rho_0(H) = \ln\rho_{0f} + U_0(H)/T_c$ yielded values of ρ_{0f} and T_c 37(1) mΩ cm and 11.2(1) K for $H||(101)$ and 39(2) mΩ cm and 11.2(1) K for $H\perp(101)$. The T_c values are consistent with the values of T_{cross} within the

TABLE I. Superconducting parameters of β -FeSe.

	$T_{c,\text{mid}}$ (K)	$(dH_{c2}/dT)_{T_c}$ (kOe/K)			$H_{c2,\text{mid}}(0)$ (kOe)	$\xi(0)$ (nm)	$H_p(0)$ (Oe)	$H_{c1}(0)$ (nm)	$\lambda(0)$ (kOe)	$H_c(0)$ $\kappa(0)$	
		Onset	Middle	Zero							
$H \parallel (101)$	9.8(2)	-30.3(6)	-26.5(6)	-25.4(4)	180(4)	4.28(5)	180(4)	75(2)	309(4)	1.76(3)	72.3(2)
$H \perp (101)$	9.8(2)	-29.6(6)	-26.6(6)	-25.5(4)	180(4)	4.28(5)	180(4)				

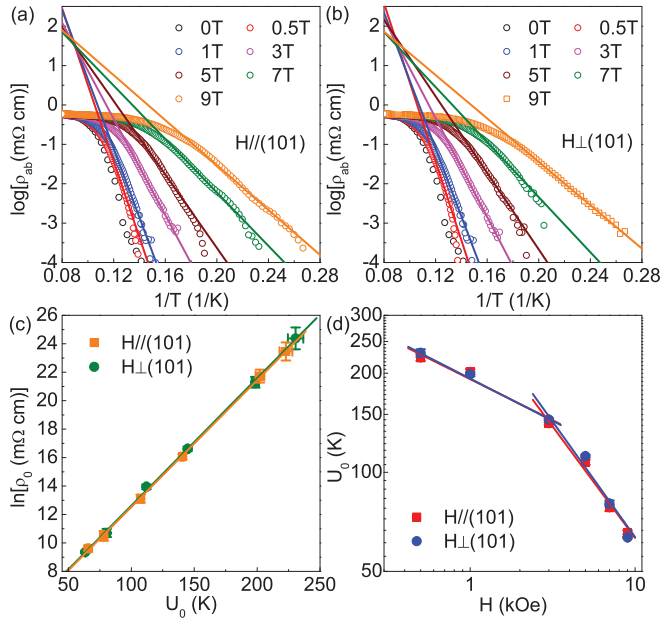


FIG. 3. (Color online) $\text{Log} \rho(T, H)$ vs $1/T$ in various fields for (a) $H \parallel (101)$ and (b) $H \perp (101)$. The corresponding solid lines are fitting results from the Arrhenius relation. (c) $\ln \rho_0(H)$ vs $U_0(H)$ derived from fitting results. (d) Field dependence of $U_0(H)$. The solid lines are power-law fits using $U_0(H) \sim H^{-\alpha}$.

error bars. $U_0(H)$ shows a power law [$U_0(H) \sim H^{-\alpha}$] field dependence for both directions [Fig. 3(d)]. For $H \parallel (101)$, $\alpha = 0.25(6)$ when $H < 30$ kOe and $\alpha = 0.68(6)$ when $H > 30$ kOe; for $H \perp (101)$, $\alpha = 0.26(2)$ when $H < 30$ kOe and $\alpha = 0.70(9)$ when $H > 30$ kOe. The weak power law decreases of $U_0(H)$ in low fields for both field directions implies that single-vortex pinning dominates in this region,²¹ followed by a quicker decrease of $U_0(H)$ in field, which could be related to a crossover to a collective flux creep regime.²²

Low-field $M(H)$ at various temperatures for $H \parallel (101)$ and $H \perp (101)$ are shown in Figs. 4(a) and 4(b), respectively. All curves exhibit linear behavior for low fields and then deviate from linearity at different field values for different temperatures. The values of H_{c1} are determined by examining the point of deviation from the linear slope of the magnetization curve. The temperature dependence of $H_{c1}(T)$ for both field directions is shown in Fig. 4(c). For $H \parallel (101)$, the $H_{c1}(T)$ can be fit well by using the formula $H_{c1}(T) = H_{c1}(0)[1 - (T/T_c)^2]$, and the obtained $H_{c1, H \parallel (101)}(0)$ is 75(2) Oe. For $H \perp (101)$, it is difficult to estimate the $H_{c1, H \perp (101)}(T)$ and obtain reliable fits. This is due to the small obtained value for H_{c1} with a relatively large error and significant demagnetization factors.

Since Fe(Te, Se) and Fe(Te, S) superconductors are within the dirty limit, we assume the same for FeSe.²³ Using estimated values of $H_{c1, H \parallel (101)}(0)$, $H_{c2}(0)$, and $\xi(0)$, we evaluate additional parameters using expressions $H_{c2}(0) = \sqrt{2} \kappa H_c(0)$ and $H_{c1}(0) = \frac{H_c(0)}{\sqrt{2} \kappa} \ln \kappa + 0.08$ where $\kappa = \lambda/\xi$ is the Ginzburg-Landau (GL) parameter and $H_c(0)$ is the thermodynamic upper critical field at $T = 0$ K.²⁴ We obtain $\kappa_{H \parallel (101)}(0) = 72.3(2)$, $H_{c, H \parallel (101)}(0) = 1.76(3)$ kOe, and penetration depth for

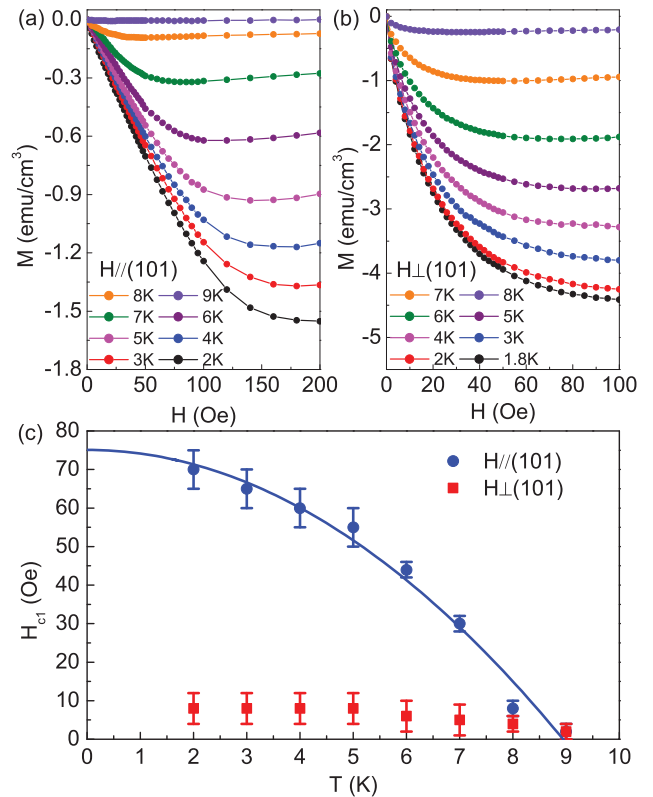


FIG. 4. (Color online) Low-field $M(H)$ of β -FeSe single crystals at various temperatures for (a) $H \parallel (101)$ and $H \perp (101)$. (c) Temperature dependence of $H_{c1}(T)$ for both field directions. The line comprises lines fitted using $H_{c1}(T) = H_{c1}(0)[1 - (T/T_c)^2]$ for $H \parallel (101)$.

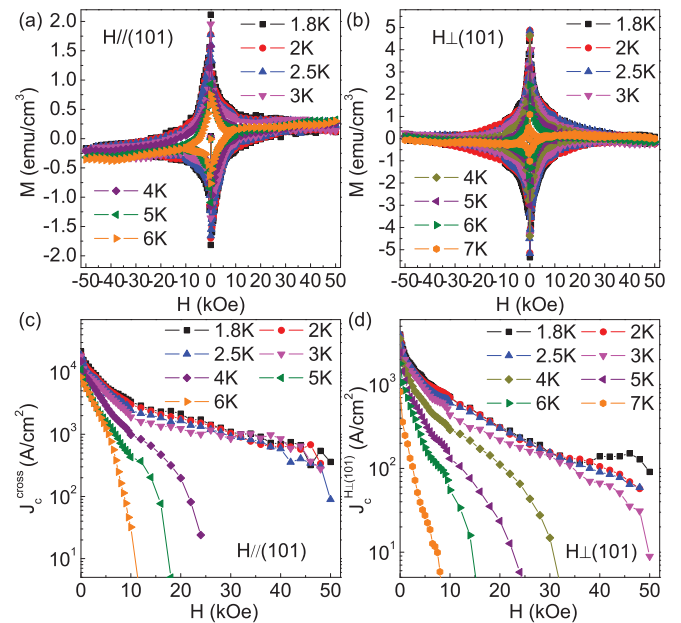


FIG. 5. (Color online) $M(H)$ loops of β -FeSe single crystals at various temperatures with fields up to 50 kOe for (a) $H \parallel (101)$ and $H \perp (101)$. (c) In-plane and (d) interplane superconducting critical currents as determined from magnetization measurements using the Bean model.

$H \parallel (101)$ $\lambda_{H \parallel (101)}(0) = 309(4)$ nm, which is somewhat smaller than in Fe(Te, Se).²³ All superconducting parameters are listed in Table I.

Figures 5(a) and 5(b) show isothermal magnetization curves $M(H)$ at various temperatures for $H \parallel (101)$ and $H \perp (101)$. The shape of the $M(H)$ curves confirms that β -FeSe is a typical type-II superconductor. The data exhibit a central peak at zero magnetic field; then the magnetization decreases continuously with an increasing magnetic field. On the other hand, there is a weak ferromagnetic (WFM) background superimposed on the superconducting $M(H)$ curve for $H \parallel (101)$. This WFM background possibly arises due to a vacancy-induced magnetic cluster.¹¹ From the irreversible parts of the $M(H)$ loops, the critical current can be determined using the Bean model.^{25,26} For a rectangular crystal with dimension $c < a < b$, when $H \perp (101)$, the in-plane critical current density $J_c^{H \perp (101)}(H)$ is given by $J_c^{H \perp (101)}(H) = 20\Delta M(H)/[a(1 - a/3b)]$, where a and b ($a < b$) are the in-plane sample sizes and $\Delta M(H)$ is the width of the magnetic hysteresis loop in emu/cm³. On the other hand, for $H \parallel (101)$, there are two different current densities: the vortex motion across the planes, $J_c^{\text{cross}}(H)$, and that parallel to the planes, $J_c^{\text{para}}(H)$. Assuming $a, b \gg (c/3)J_c^{\text{para}}(H)/J_c^{\text{cross}}(H)$,²⁶ we obtain $J_c^{\text{cross}}(H) \approx 20\Delta M(H)/c$. The magnetic field dependence of $J_c^{\text{cross}}(H)$ and $J_c^{H \perp (101)}(H)$ is shown in Figs. 4(c) and 4(d), respectively. It should be noted that for $H \parallel (101)$, the WFM background has only a minor effect on the calculation of $\Delta M(H)$, because of the very weak moment contribution of WFM. The error of calculated $J_c^{\text{cross}}(H)$ is about 10% without subtracting the WFM background. It can be seen that $J_c^{\text{cross}}(0)$ and $J_c^{H \perp (101)}(0)$

at 1.8 K are about 2.2×10^4 and 4×10^3 A/cm², which are much smaller than in Fe(Te, Se) and Fe(Te, S) at the same temperature.^{27,28} The ratio of $J_c^{\text{cross}}(H)/J_c^{H \perp (101)}(H)$ is about 5.4 at 1.8 K. Moreover, above 4 K, the critical current densities decrease with the applied field more quickly than below 4 K, suggesting that the pinning mechanism may change at 4 K.

IV. CONCLUSION

In summary, we present the superconducting properties of β -FeSe single crystals. The results indicate that the $H_{c2}(T)$ is isotropic and the spin-paramagnetic effect may be the dominant pair-breaking mechanism for $H \parallel (101)$ and $H \perp (101)$. The calculated GL parameter κ indicates that β -FeSe is a typical type-II superconductor with a large κ . The resistivity exhibits clear Arrhenius TAFF behavior with a crossover from a single-vortex pinning region to a collective creep region for both field directions. On the other hand, the critical current density for field along the (101) plane is about five times larger than for a field normal to the (101) plane but still smaller than in Fe(Te, Se) and Fe(Te, S) at the same temperature.

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